

SILICON EPITAXIAL WAVEGUIDE SWITCHING DIODES

The MA-47000 series of silicon epitaxial switching diodes is recommended for use in microwave switches, modulators, voltage controlled microwave attenuators, phase shifters and limiters as well as other microwave power control applications. Each of these devices, ranging in frequency from 7.5 GHz to 17.5 GHz, is housed in an axial pronged hermetically sealed glass package.

When used as RF switches, these diode types are mounted in a resonant waveguide mount such that positive bias produces minimum insertion loss while negative bias produces a large impedance mismatch with resulting high isolation values. The switching time is less than 10 ns for all devices in this series.

MODEL NUMBER	CASE STYLE	CENTER FREQ. ¹ (GHz)	WAVEGUIDE DESIG.	MAX. INSERTION LOSS ² (dB)	MAX. INCIDENT CW PWR. (WATTS)	MIN. ISOL. ³ (dB)
MA-47067	151	7.5	WR112	1.2	4.0	25
MA-47068	151	8.0	WR112	1.2	4.0	25
MA-47069	151	8.5	WR112	1.2	3.5	25
MA-47070	151	9.0	WR112	1.2	2.5	25
MA-47071	151	9.5	WR112	1.2	2.0	25
MA-47105	151	10.0	WR90	0.75	4.0	25
MA-47106	151	10.5	WR90	0.75	3.5	25
MA-47107	151	11.0	WR90	0.75	2.5	25
MA-47108	151	11.5	WR90	0.75	2.0	25
MA-47109	152	12.0	WR90	0.75	2.0	25
MA-47126	152	13.0	WR62	0.75	4.0	25
MA-47127	152	13.5	WR62	0.75	4.0	20
MA-47128	152	14.0	WR62	0.75	4.0	20
MA-47129	152, 164	14.5	WR62	0.75	3.5	20
MA-47130	164	15.0	WR62	0.75	3.5	20
MA-47131	164	15.5	WR62	0.75	2.5	20
MA-47132	164	16.0	WR62	0.75	2.0	20
MA-47133	164	16.5	WR62	0.75	2.0	20
MA-47134	164	17.0	WR62	0.75	2.0	20
MA-47135	164	17.5	WR62	1.0	2.0	20

NOTES:

1. VSWR is less than 1.3:1 at the center frequency.
2. Insertion loss is measured at a forward bias current of 50 mA.
3. Isolation is measured at a reverse bias voltage of 50 volts.